

Final Product/Process Change Notification Document #: FPCN21292XG

Issue Date: 16 November 2017

Title of Change:	Qualification of VHVIC (Very High Voltage IC) Technology at AFSM (Aizu Fujitsu Semiconductor Manufacturing) Japan – Phase 2			
Proposed first ship date:	23 February 2018			
Contact information:	Contact your local ON Semiconductor Sales Office or <scott.brow@onsemi.com></scott.brow@onsemi.com>			
Samples:	Contact your local ON Semiconductor Sales Office			
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or <tomas.vajter@onsemi.com>.</tomas.vajter@onsemi.com>			
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com>			
Change Part Identification:	Product will be identified by having a date code of 1808 or newer. As material from different FABS cannot be combined in to (1) reel, product from AFSM will show CS: JP (Custom Source) on the label of the reel and box. Please see sample MPN on Page 2 at the following URL http://www.onsemi.com/pub/Collateral/LABELRM-D.PDF to see the location of the CS Identifier.			
Change category:	✓ Wafer Fab Change ☐ Assembly Change ☐ Test Change ☐ Other			
Change Sub-Category(s): Manufacturing Site Change Manufacturing Process Cha	Shipping/Packaging/iviarking			
Sites Affected:	ON Semiconductor Sites: None External Foundry/Subcon Sites: Aizu Fujitsu, Japan			
Description and Purpose:				
ON Semiconductor would like to inform our customers that we have qualified our Very High Voltage IC (VHVIC) technology at the AFSM (Aizu Fujitsu Semiconductor Manufacturing) FAB in Aizu, Japan. This qualification enables expanded capacity for this technology.				
All products listed in this FPCN may be dual sourced from either its current ON Semiconductor Wafer FAB in Gresham, OR or AFSM. This is				

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Reliability Data Summary:

QV DEVICE NAME: NCP1236BD65R2G PACKAGE: SOIC 8 (Less Pin 7)

Test	Specification	Condition	Interval	Results
HTOL	JESD22-A108	Ta=125°C, 500V	1000 hrs	0/231
HTSL	JESD22-A103	Ta= 150°C	1000 hrs	0/231
PC-TC	JESD22-A104	Ta= -65°C to +150°C	500 cyc	0/231
HAST	JESD22-A110	130°C, 85% RH, 18.8psig, bias	96 hrs	0/231
PC-uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs	0/231
PC	J-STD-020 JESD-A113	MSL 1 @ 260 °C		0/693

QV DEVICE NAME: NCP1396ADR2G

PACKAGE: SOIC-16

Test	Specification	Condition	Interval	Results
HTOL	JESD22-A108	Ta=125°C, 600V	1000 hrs	0/231
HTSL	JESD22-A103	Ta= 150°C	1000 hrs	0/231
PC-TC	JESD22-A104	Ta= -65°C to +150°C	500 cyc	0/231
HAST	JESD22-A110	130°C, 85% RH, 18.8psig, bias	96 hrs	0/231
PC-uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs	0/231
PC	J-STD-020 JESD-A113	MSL 1 @ 260 °C		0/693

Electrical Characteristic Summary:

As the process was copied and matched from the sending FAB, electrical characteristics are not impacted by this change. Characterization reports are available upon request

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List of Affected Parts:

Part Number	Qualification Vehicle	
NCP1218AD65R2G		
NCP1219AD100R2G		
NCP1219AD65R2G		
NCP1219BD100R2G		
NCP1219BD65R2G		
NCP1247AD065R2G		
NCP1247AD100R2G	NCP1236BD65R2G	
NCP1247BD065R2G		
NCP1247BD100R2G		
NCP1247CD065R2G		
NCP1247CD100R2G		
NCP1247DD065R2G		
NCP1247DD100R2G		
NCP1248AD065R2G		
NCP1248AD100R2G		
NCP1271D100R2G		
NCP1271D65R2G		
NCP1631DR2G		
NCP1654BD133R2G		
NCP1654BD200R2G	1	
NCP1654BD65R2G		
NCP1397ADR2G	NCP1396ADR2G	
NCP1397BDR2G		

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